30V Dual N-Channel MOSFETs

General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
30V	13mΩ	35A

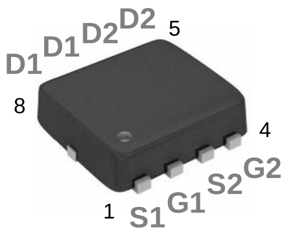
Features

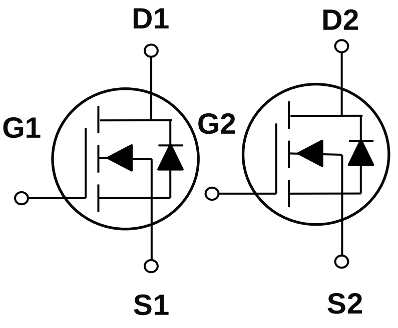
- *30V,35A, RDS(ON) =13mΩ @VGS = 10V*
- *Improved dv/dt capability*
- *Fast switching*
- *100% EAS Guaranteed*
- *Green Device Available*

Applications

- *MB / VGA / Vcore*
- *POL Applications*
- *SMPS 2nd SR*

PPAK3X3 Dual Pin Configuration





Absolute Maximum Ratings **(Tc=25℃ unless otherwise noted)**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	35	A
	Drain Current – Continuous (T_C=100℃)	22	A
I_{DM}	Drain Current – Pulsed[1]	140	A
EAS	Single Pulse Avalanche Energy[2]	13	mJ
IAS	Single Pulse Avalanched Current[2]	16	A
P_D	Power Dissipation (T_C=25℃)	27	W
	Power Dissipation – Derate above 25℃	0.22	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{θJA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{θJC}$	Thermal Resistance Junction to Case	---	4.6	℃/W

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Electrical Characteristics **(T_J=25℃, unless otherwise noted)**

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
△BV_{DSS}/△T_J	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.04	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=30V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance[3]	V_{GS}=10V , I_D=10A	---	10	13	mΩ
		V_{GS}=4.5V , I_D=5A	---	14	16	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.8	2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4	---	mV/℃
gfs	Forward Transconductance	V_{DS}=10V , I_D=3A	---	6	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[3,4]	V_{DS}=15V , V_{GS}=4.5V , I_D=5A	---	7.4	12	nC
Q_{gs}	Gate-Source Charge[3,4]		---	2.3	5	
Q_{gd}	Gate-Drain Charge[3,4]		---	3	6	
$T_{d(on)}$	Turn-On Delay Time[3,4]	V_{DD}=15V , V_{GS}=10V , R_G=6Ω I_D=1A	---	3.8	7	ns
T_r	Rise Time[3,4]		---	10	19	
$T_{d(off)}$	Turn-Off Delay Time[3,4]		---	22	42	
T_f	Fall Time[3,4]		---	6.6	13	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , F=1MHz	---	620	900	pF
C_{oss}	Output Capacitance		---	85	125	
C_{rss}	Reverse Transfer Capacitance		---	60	90	
Rg	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	---	2.8	5.6	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	35	A
I_{SM}	Pulsed Source Current[3]		---	---	70	A
V_{SD}	Diode Forward Voltage[3]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=16A.,R_G=25Ω,Starting T_J=25℃.
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

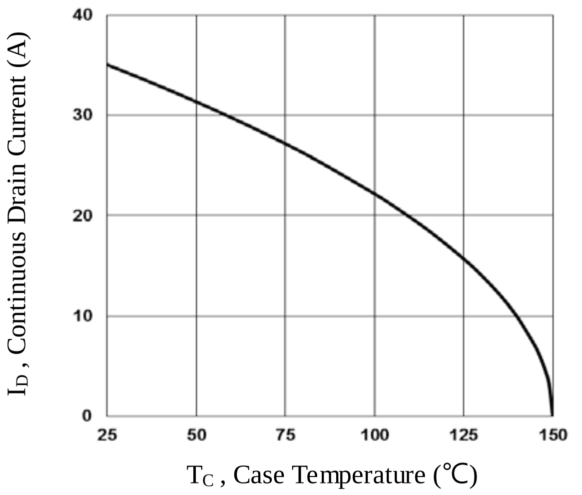


Fig.1 Continuous Drain Current vs. T_C

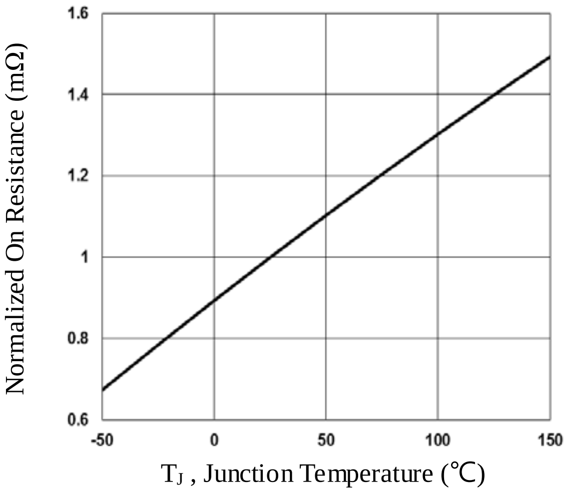


Fig.2 Normalized RDSON vs. T_J

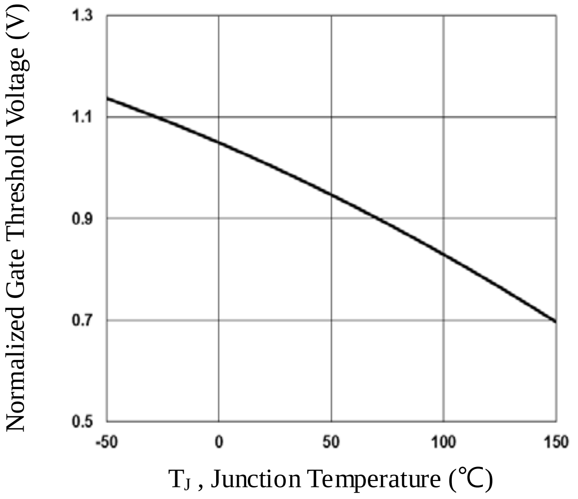


Fig.3 Normalized V_{th} vs. T_J

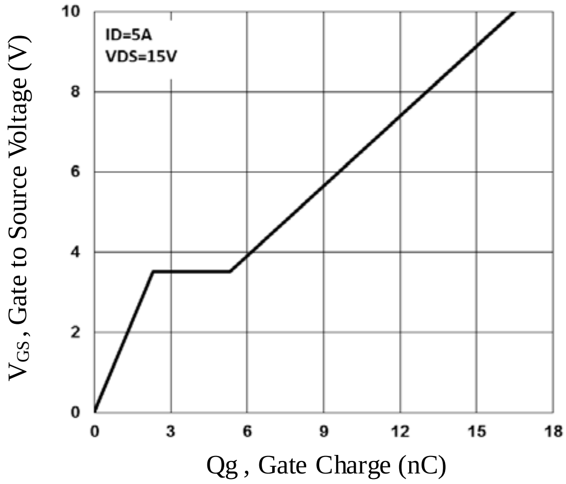


Fig.4 Gate Charge Waveform

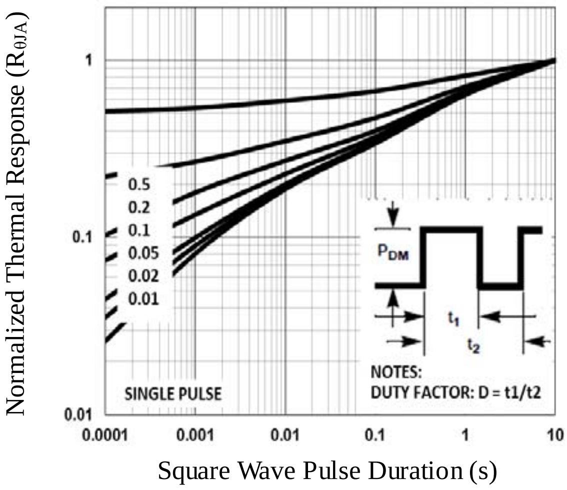


Fig.5 Normalized Transient Response

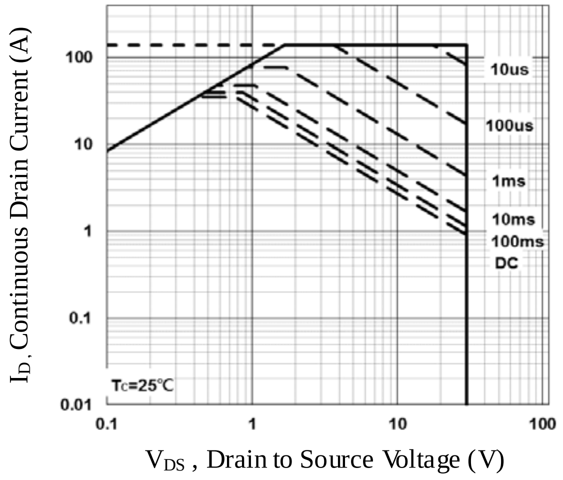


Fig.6 Maximum Safe Operation Area

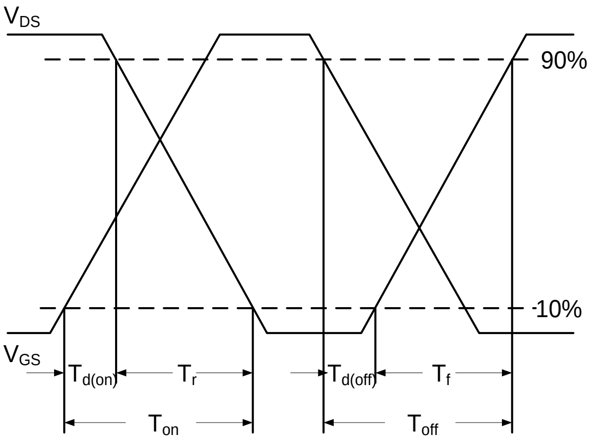


Fig.7 Switching Time Waveform

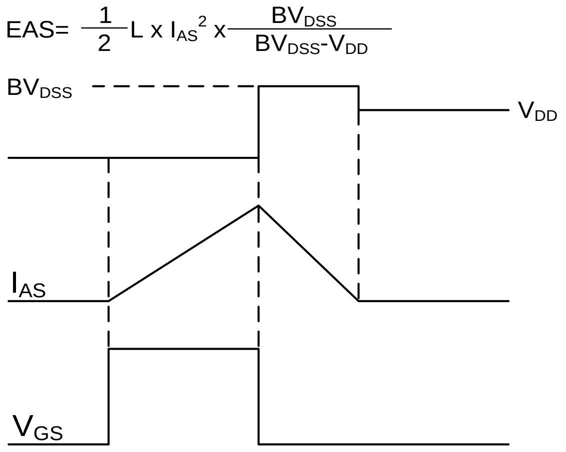
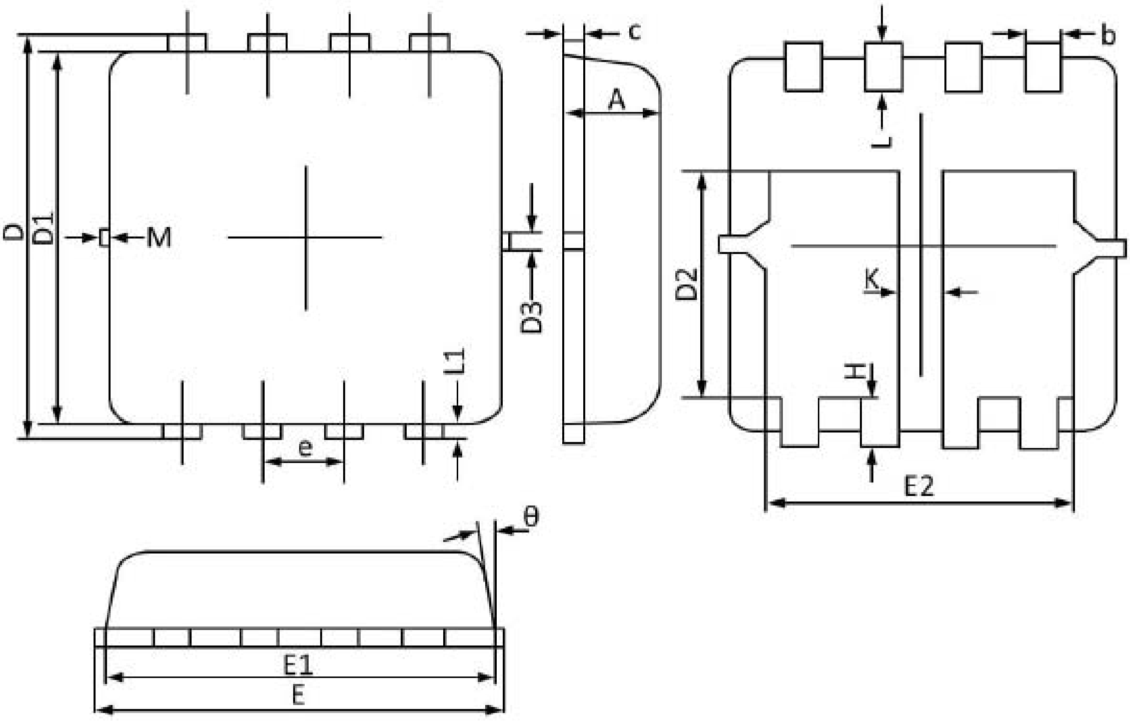


Fig.8 EAS Waveform

PPAK3X3 Dual PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
b	0.250	0.350	0.010	0.013
c	0.100	0.250	0.004	0.009
D	3.250	3.450	0.128	0.135
D1	3.000	3.200	0.119	0.125
D2	1.780	1.980	0.070	0.077
D3	0.130 REF		0.005 REF	
E	3.200	3.400	0.126	0.133
E1	3.000	3.200	0.119	0.125
E2	2.390	2.590	0.094	0.102
e	0.650 BSC		0.026 BSC	
H	0.300	0.500	0.011	0.019
L	0.300	0.500	0.011	0.019
L1	0.130 REF		0.005 REF	
K	0.300 REF		0.012 REF	
θ	0°	12°	0°	12°
M	0.150 REF		0.006 REF	